

Serial No. 09/008,531
Atty. Docket No. MIO 0012 V2

Appendix

In the Claims

Please cancel claims 26-30, 35-36, 40-43, and 48.

21. (Four times Amended) 21. A process for making a semiconductor device comprising the steps of:

- providing a substrate having at least one semiconductor layer;
- forming an underlayer having an opening over the at least one semiconductor layer;
- forming a layer of conductive material over the underlayer and said opening having a topography that includes a substantially vertical component;
- forming an overlayer over the said layer of conductive material;
- etching a contact hole in said overlayer and in an overetch amount of the substantially vertical component; and
- forming a contact in said contact hole disposed adjacent to and directly contacting said vertical component.

31. (Thrice Amended) A process for making a semiconductor device comprising:

- providing a substrate having at least one semiconductor layer;
- forming a structure having an opening in said at least one semiconductor layer;
- forming a layer of conductive material over said at least one semiconductor layer;
- filling said opening with said conductive material to form a substantially vertical component;
- [forming an opening in said at least one semiconductor layer, wherein said opening includes sidewalls;
- forming a conductive layer over said at least one semiconductor layer and said opening so that said conductive layer has a topography that includes a substantially vertical component;]
- forming an overlayer over said [conductive layer] layer of conductive material;

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forming a contact in said overlayer and in said vertical component disposed adjacent to and contacting said vertical component; and filling said contact with a conducting material.

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MAR 12 2003
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